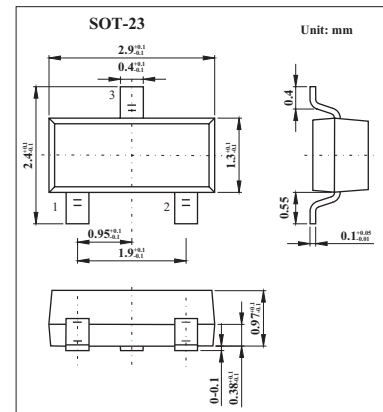


## Silicon Epitaxial Schottky Barrier Diode

## 1SS350

## ■ Features

- Small interterminal capacitance ( $C=0.69\text{pF typ}$ ).
- Low forward voltage ( $V_F=0.23\text{V max}$ ).
- High breakdown voltage ( $V_R=55\text{V}$ ).
- Very small-sized package permitting the 1SS350-applied sets to be made small and slim.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	5	V
Forward Current	$I_F$	30	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F = 1\text{ mA}$			0.23	V
Forward Current	$I_F$	$V_F = 0.5\text{ V}$	30			mA
Reverse Current	$I_R$	$V_R = 0.5\text{ V}$			25	$\mu\text{ A}$
Interterminal Capacitance	$C$	$V_R = 0.2\text{ V}, f = 1\text{ MHz}$		0.69	0.9	pF

## ■ Marking

Marking	BH
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